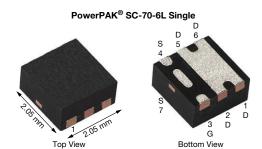


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Vishay Siliconix

P-Channel 12 V (D-S) MOSFET



Marking code: BS

PRODUCT SUMMARY	
V _{DS} (V)	-12
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.029
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5 \text{ V}$	0.034
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.8 \text{ V}$	0.044
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.5 \text{ V}$	0.100
Q _g typ. (nC)	23
I _D (A) ^a	-12
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-70 package
 - Small footprint area
 - Low on-resistance

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

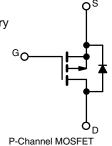


ROHS COMPLIANT HALOGEN

of **FREE**

APPLICATIONS

 Load switch, PA switch, and battery switch for portable devices



ORDERING INFORMATION	
Package	PowerPAK SC-70
Load (Dh) free and helegan free	SiA413ADJ-T4-GE3
Lead (Pb)-free and halogen-free	SiA413ADJ-T1-GE3

ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unless	otherwise noted	d)	
PARAMETER		SYMBOL LIMIT		UNIT
Drain-source voltage		V _{DS}	-12	V
Gate-source voltage		V_{GS}	¬	
	T _C = 25 °C		-12 ^a	
Continuous dusin surrent (T. 150 °C)	T _C = 70 °C		-12 ^a	
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	I _D	-10 ^{b, c}	
	T _A = 70 °C		-8 b, c	A
Pulsed drain current (t = 300 μs)		I _{DM}	-40	
Continuous source-drain diode current	T _C = 25 °C	1	-12 ^a	
Continuous source-drain diode current	T _A = 25 °C	I _S	-2.9 ^{b, c}	
	T _C = 25 °C		19	
Maximum pawar dissination	T _C = 70 °C		12	_ w
Maximum power dissipation	T _A = 25 °C	P _D	3.5 ^{b, c}	VV
	T _A = 70 °C		2.2 b, c	
Operating junction and storage temperature ran	nge	T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature)) d, e		260	

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	28	36	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	5.3	6.5	C/VV				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 5 s
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 80 °C/W



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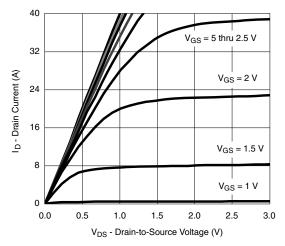
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static			•		l	I.
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-12	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$		-	-11	-	mV/°C
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = -250 \mu A$	-	2.7	-	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-	-1	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	-	-	± 100	nA
Zana anta calta na disaisa accimant		V _{DS} = -12 V, V _{GS} = 0 V	-	-	-1	. ^
Zero gate voltage drain current	I _{DSS}	V _{DS} = -12 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10	μΑ
On-state drain current a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-20	-	-	Α
		$V_{GS} = -4.5 \text{ V}, I_D = -6.7 \text{ A}$	-	0.024	0.029	
Duning and an atota variation of 3		$V_{GS} = -2.5 \text{ V}, I_D = -6.2 \text{ A}$	-	0.028	0.034	
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = -1.8 \text{ V}, I_D = -2.3 \text{ A}$	-	0.036	0.044	Ω
		V _{GS} = -1.5 V, I _D = -1 A	-	0.050	0.100	
Forward transconductance a	9 _{fs}	$V_{DS} = -10 \text{ V}, I_D = -6.7 \text{ A}$	-	30	-	S
Dynamic ^b			•			
Input capacitance	C _{iss}		-	1800	-	pF
Output capacitance	C _{oss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	450	-	
Reverse transfer capacitance	C _{rss}		-	390	-	
Tatal nata abauma	0	$V_{DS} = -6 \text{ V}, V_{GS} = -8 \text{ V}, I_D = -10 \text{ A}$	-	38	57	nC
Total gate charge	Qg		-	23	35	
Gate-source charge	Q_{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}$	-	3	-	
Gate-drain charge	Q _{gd}		-	6.5	-	
Gate resistance	R _q	f = 1 MHz	-	7	-	Ω
Turn-on delay time	t _{d(on)}		-	20	30	-
Rise time	t _r	$V_{DD} = -6 \text{ V}, R_L = 0.75 \Omega,$	-	40	60	
Turn-off delay time	t _{d(off)}	$I_D \cong -8 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$	-	65	100	
Fall time	t _f		-	40	60	
Turn-on delay time	t _{d(on)}		-	10	15	ns
Rise time	t _r	$V_{DD} = -6 \text{ V}, R_L = 0.75 \Omega,$	-	12	20	- - -
Turn-off delay time	t _{d(off)}	$I_D\cong$ -8 A, V_{GEN} = -8 V, R_g = 1 Ω	-	70	105	
Fall time	t _f		-	40	60	
Drain-Source Body Diode Characterist	ics					
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	-12	
Pulse diode forward current			-	-	40	_ A
Body diode voltage	V _{SD}	$I_S = -8 \text{ A}, V_{GS} = 0 \text{ V}$	-	-0.8	-1.2	V
Body diode reverse recovery time	t _{rr}	**	-	40	60	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = -8 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	20	30	nC
Reverse recovery fall time	t _a	T _J = 25 °C	-	14	-	
	, ~			1	1	ns

Notes

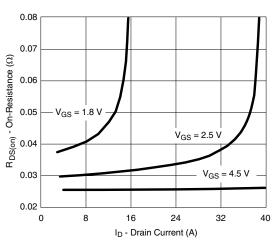
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

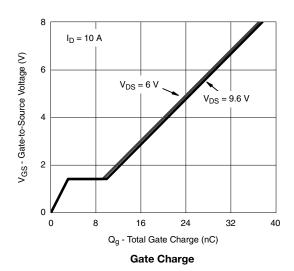


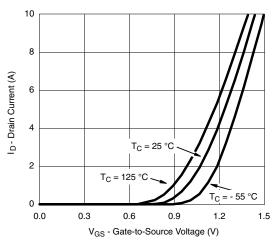


Output Characteristics

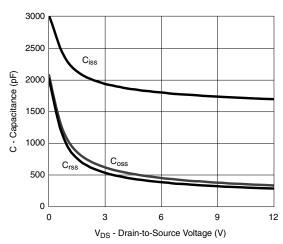


On-Resistance vs. Drain Current and Gate Voltage

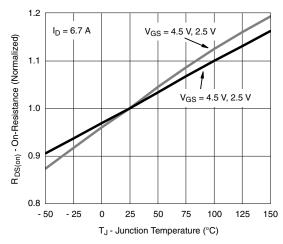




Transfer Characteristics

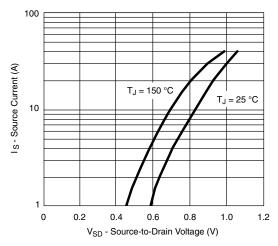


Capacitance

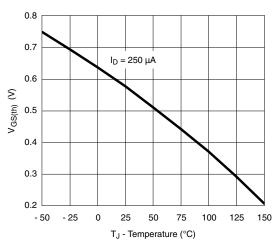


On-Resistance vs. Junction Temperature

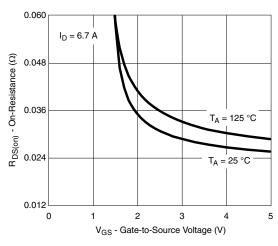




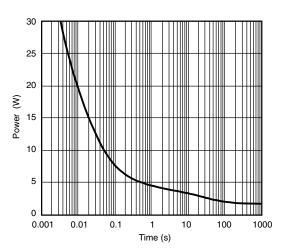
Source-Drain Diode Forward Voltage



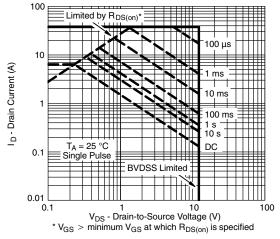
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

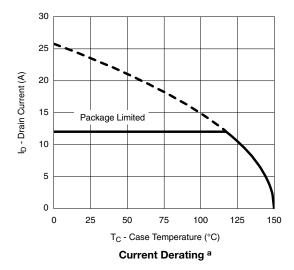


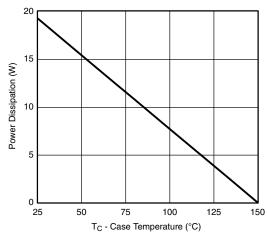
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient





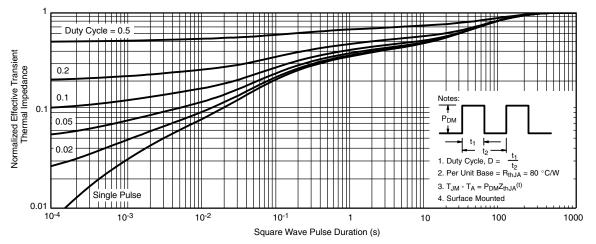


Power Derating

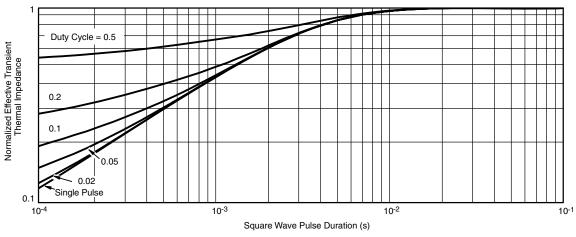
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63650.

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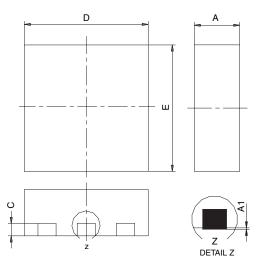
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD						
DIM	M	ILLIMETER	RS		INCHES	CHES		MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC			
K		0.275 TYP			0.011 TYP	1	0.275 TYP			0.011 TYP			
K1		0.400 TYP			0.016 TYP	1	0.320 TYP			0.013 TYP			
K2		0.240 TYP			0.009 TYP			0.252 TYP			0.010 TYP		
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP			0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 - Bey C. 06-Aug-07													

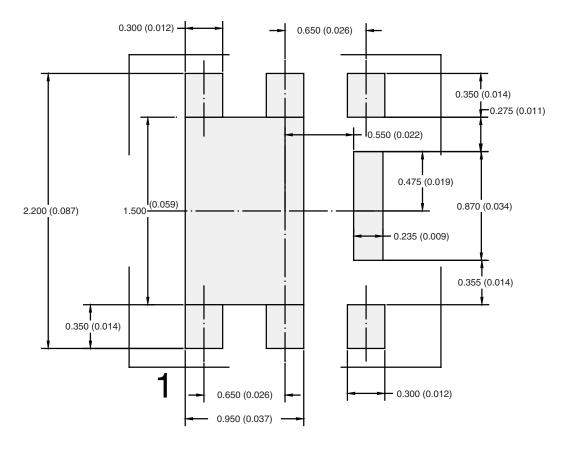
DWG: 5934

Document Number: 73001 06-Aug-07

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RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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